

**2SA1341,
2SC3395**

2018A

PNP/NPN Epitaxial Planar
Silicon Transistors

T-37-13

T-35-11

Switching Applications

(with Bias Resistances $R_1=47k\Omega$, $R_2=47k\Omega$)

©1283C

Applications

- Switching circuit, inverter circuit, interface circuit, driver circuit.

Features

- Built-in bias resistor ($R_1=47k\Omega$, $R_2=47k\Omega$).
- Small-sized package (CP).

(): 2SA1341

Absolute Maximum Ratings/ $T_a=25^\circ\text{C}$

			unit
Collector to Base Voltage	V_{CBO}	(-) 50	V
Collector to Emitter Voltage	V_{CEO}	(-) 50	V
Emitter to Base Voltage	V_{EBO}	(-) 10	V
Collector Current	I_C	(-) 100	mA
Peak Collector Current	i_{cp}	(-) 200	mA
Collector Dissipation	P_C	200	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to $+150$	$^\circ\text{C}$

Electrical Characteristics/ $T_a=25^\circ\text{C}$

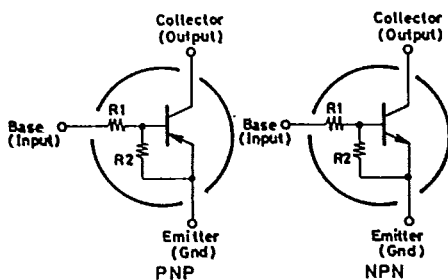
			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40\text{V}$, $I_E=0$			(-) 0.1	μA
Collector Cutoff Current	I_{CEO}	$V_{CE}=(-)40\text{V}$, $I_B=0$			(-) 0.5	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5\text{V}$, $I_C=0$	(-) 30	(-) 53	(-) 80	μA
DC Current Gain	h_{FE}	$V_{CE}=(-)5\text{V}$, $I_C=(-)5\text{mA}$	50			
Gain Band-width product	f_T	$V_{CE}=(-)10\text{V}$, $I_C=(-)5\text{mA}$		250 (200)		MHz
Output Capacitance	c_{ob}	$V_{CB}=(-)10\text{V}$, $f=1\text{MHz}$		3.5 (5.3)		pF
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)5\text{mA}$, $I_B=(-)0.25\text{mA}$		(-) 0.1	(-) 0.3	V

Continued on next page.

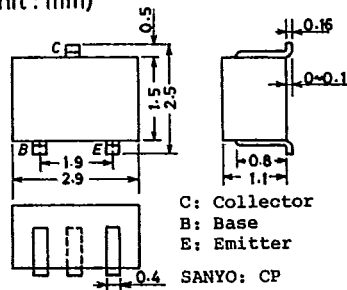
Marking

2SA1341:BL, 2SC3395:BY

Electrical Connection



Case Outline 2018A (unit: mm)



2SA1341/2SC3395

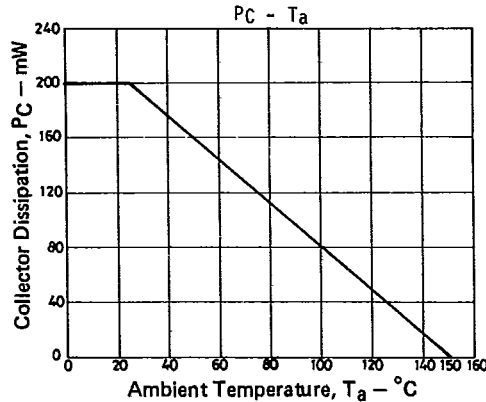
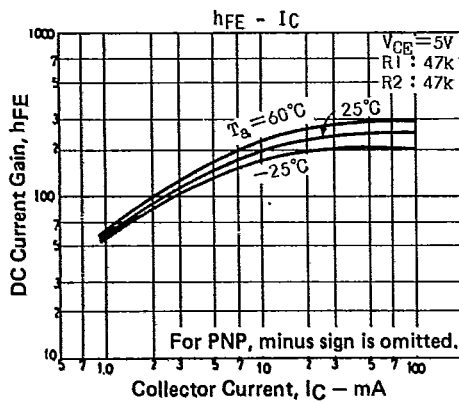
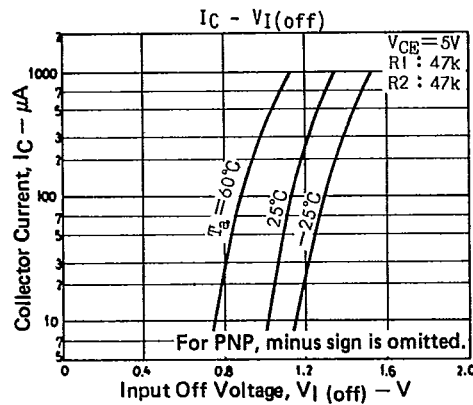
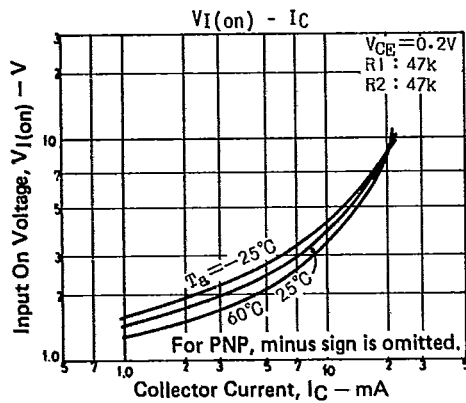
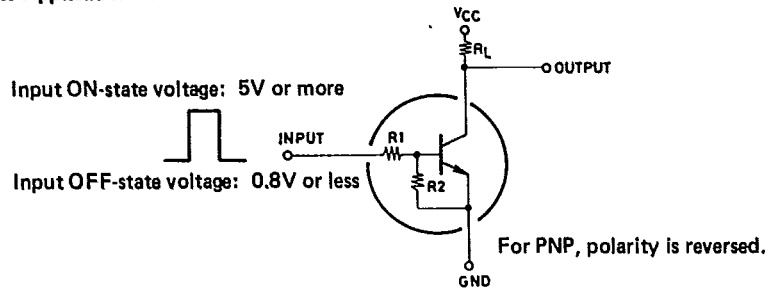
T-37-13

T-35-11

Continued from preceding page.

			min	typ	max	unit
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)10\mu A, I_E=0$	(-)50			V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)100\mu A, R_{BE}=\infty$	(-)50			V
Input Off Voltage	$V_{I(off)}$	$V_{CE}=(-)5V, I_C=(-)100\mu A$	(-)0.8	(-)1.1	(-)1.5	V
Input On Voltage	$V_{I(on)}$	$V_{CE}=(-)0.2V, I_C=(-)5mA$	(-)1.0	(-)2.5	(-)5.0	V
Input Resistance	R_1		32	47	62	k Ω
Input Resistance Ratio	R_1/R_2		0.9	1.0	1.1	-

■ Sample Application Circuit

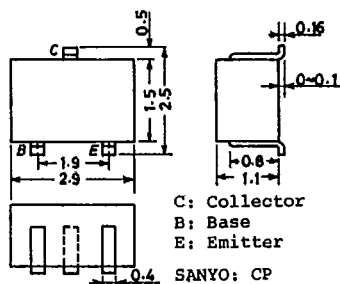


T-91-20

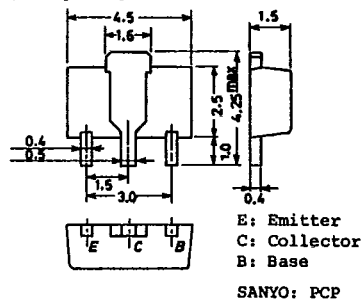
CASE OUTLINES OF SURFACE MOUNT TRANSISTORS

- All of Sanyo surface mount transistor case outlines are illustrated below.
- All dimensions are in mm, and dimensions which are not followed by min. or max. are represented by typical values.
- No marking is indicated.

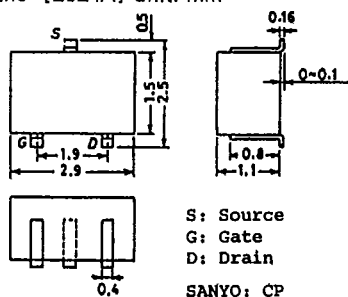
Case Outline—[2018A] unit: mm



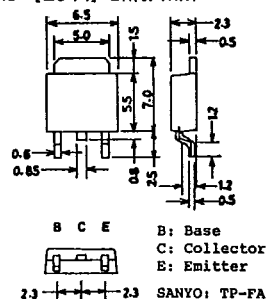
Case Outline—[2038] unit: mm



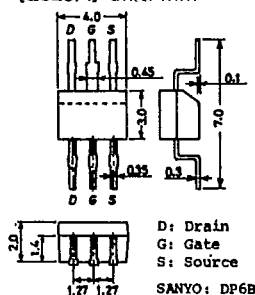
Case Outline—[2024A] unit: mm



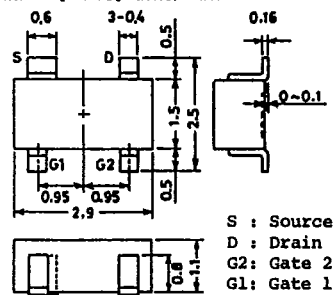
Case Outline—[2044] unit: mm



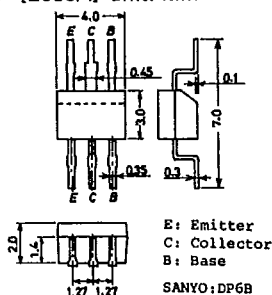
Case Outline—[2028A] unit: mm



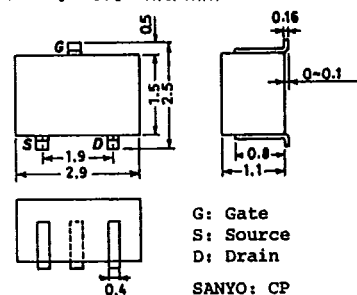
Case Outline—[2046] unit: mm



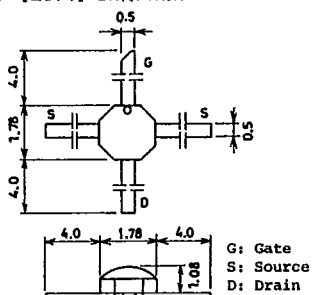
Case Outline—[2030A] unit: mm



Case Outline—[2050] unit: mm

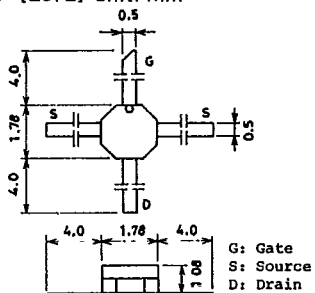


Case Outline—[2071] unit: mm



T-9120

Case Outline—[2072] unit: mm



Case Outline—[2073] unit: mm

